

# FQA47P06

## 60V P-Channel MOSFET

### General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand a high energy pulse in the avalanche and commutation modes. These devices are well suited for low voltage applications such as automotive, DC/DC converters, and high efficiency switching for power management in portable and battery operated products.

### Features

- -55A, -60V,  $R_{DS(on)} = 0.026\Omega @ V_{GS} = -10\text{ V}$
- Low gate charge ( typical 84 nC)
- Low Crss ( typical 320 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



### Absolute Maximum Ratings

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	FQA47P06	Units
$V_{DSS}$	Drain-Source Voltage	-60	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	-55	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	-38.9	A
$I_{DM}$	Drain Current - Pulsed	(Note 1)	A
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	214	W
	- Derate above $25^\circ\text{C}$	1.43	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.7	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C}/\text{W}$

**Elerical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = -250 \mu\text{A}$	-60	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	-0.06	--	$\text{V}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = -60 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$	--	--	-1	$\mu\text{A}$
		$V_{\text{DS}} = -48 \text{ V}$ , $T_C = 150^\circ\text{C}$	--	--	-10	$\mu\text{A}$
$I_{\text{GSSF}}$	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = -25 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
$I_{\text{GSSR}}$	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = 25 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA

**On Characteristics**

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = -250 \mu\text{A}$	-2.0	--	-4.0	V
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = -10 \text{ V}$ , $I_D = -27.5 \text{ A}$	--	0.021	0.026	$\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = -30 \text{ V}$ , $I_D = -27.5 \text{ A}$ (Note 4)	--	22	--	S

**Dynamic Characteristics**

$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = -25 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$	--	2800	3600	pF
$C_{\text{oss}}$	Output Capacitance		--	1300	1700	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	320	420	pF

**Switching Characteristics**

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = -30 \text{ V}$ , $I_D = -23.5 \text{ A}$ , $R_G = 25 \Omega$	--	50	110	ns
$t_r$	Turn-On Rise Time		--	450	910	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	100	210	ns
$t_f$	Turn-Off Fall Time		--	195	400	ns
$Q_g$	Total Gate Charge	$V_{\text{DS}} = -48 \text{ V}$ , $I_D = -47 \text{ A}$ , $V_{\text{GS}} = -10 \text{ V}$	--	84	110	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	18	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	44	--	nC

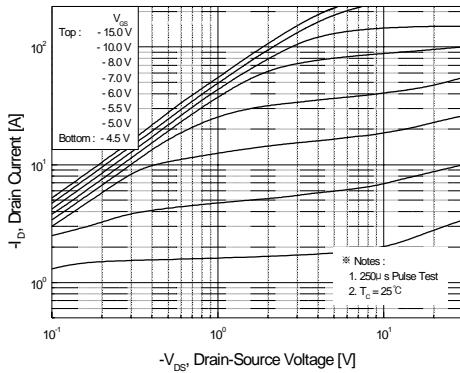
**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	-55	A
$I_{\text{SM}}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-220	A
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = -55 \text{ A}$	--	--	$-4.0$
$t_{\text{rr}}$	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = -47 \text{ A}$ , $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	130	--
$Q_{\text{rr}}$	Reverse Recovery Charge		--	0.55	--

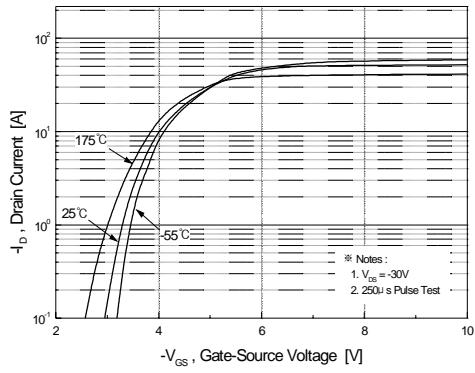
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 0.315 \text{ mH}$ ,  $I_{AS} = -55 \text{ A}$ ,  $V_{DD} = -25 \text{ V}$ ,  $R_G = 25 \Omega$ . Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq -47 \text{ A}$ ,  $dI/dt \leq 300 \text{ A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{\text{DSS}}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300 \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

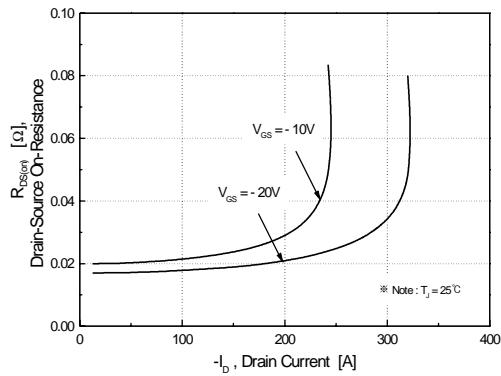
## Typical Characteristics



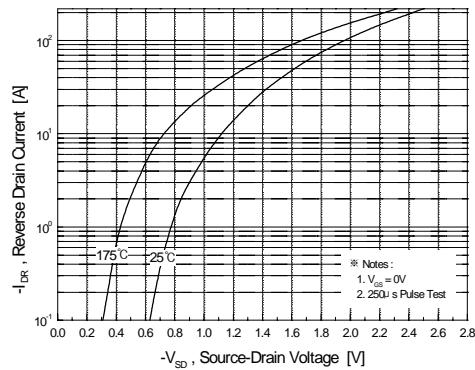
**Figure 1. On-Region Characteristics**



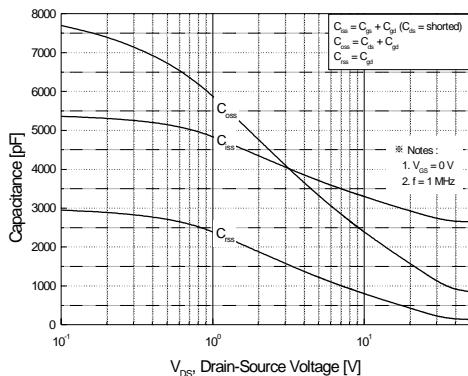
**Figure 2. Transfer Characteristics**



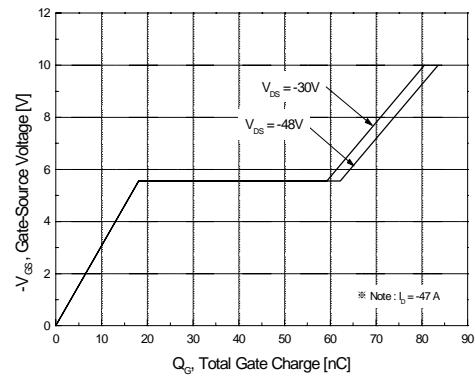
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**